

Title (en)
METHOD FOR VALIDATING THE THERMAL HISTORY OF A SEMICONDUCTOR INGOT

Title (de)
VERFAHREN ZUR VALIDIERUNG DER THERMISCHEN HISTORIE EINES HALBLEITERBLOCKS

Title (fr)
MÉTHODE DE VALIDATION DE L'HISTOIRE THERMIQUE D'UN LINGOT SEMI-CONDUCTEUR

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Application
EP 18814626 A 20181212

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Abstract (en)
[origin: WO2019115574A1] The invention relates to an experimental method for validating a thermal history of a semiconductor ingot obtained by simulation of a crystallization process. This method comprises the following steps: a) measuring the concentration of interstitial oxygen in a portion of the semiconductor ingot; b) calculating a theoretical value of the concentration of thermal donors formed during the crystallization process, from the measurement of the concentration of interstitial oxygen and from the thermal history in the portion of the semiconductor ingot; c) measuring an experimental value of the concentration of thermal donors in the portion of the semiconductor ingot; and d) comparing the theoretical and experimental values of the concentration of thermal donors.

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Citation (search report)
See references of WO 2019115574A1

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